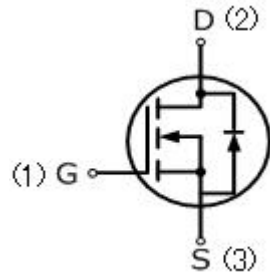


180N10CB

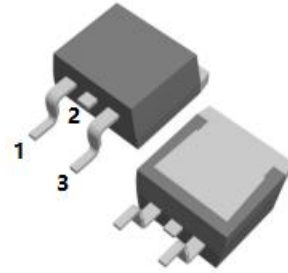
180Amps, 100 Volts N-CHANNEL MOSFET

FEATURE

- 180A, 100V, $R_{DS(ON)MAX}=7.0m\Omega$, $V_{GS}=10V/20A$
- Low gate charge
- Low C_{iss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS 2.0 Compliant



TO-263CB-2L



Absolute Maximum Ratings ($T_C=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	180N10CB	UNIT
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current $T_C=25^\circ\text{C}$	I_D	180	A
Continuous Drain Current $T_C=100^\circ\text{C}$	I_D	108	
Pulsed Drain Current (Note 1)	I_{DM}	720	
Single Pulse Avalanche Energy (Note 2)	E_{AS}	380	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	260	$^\circ\text{C}$

Thermal Characteristics

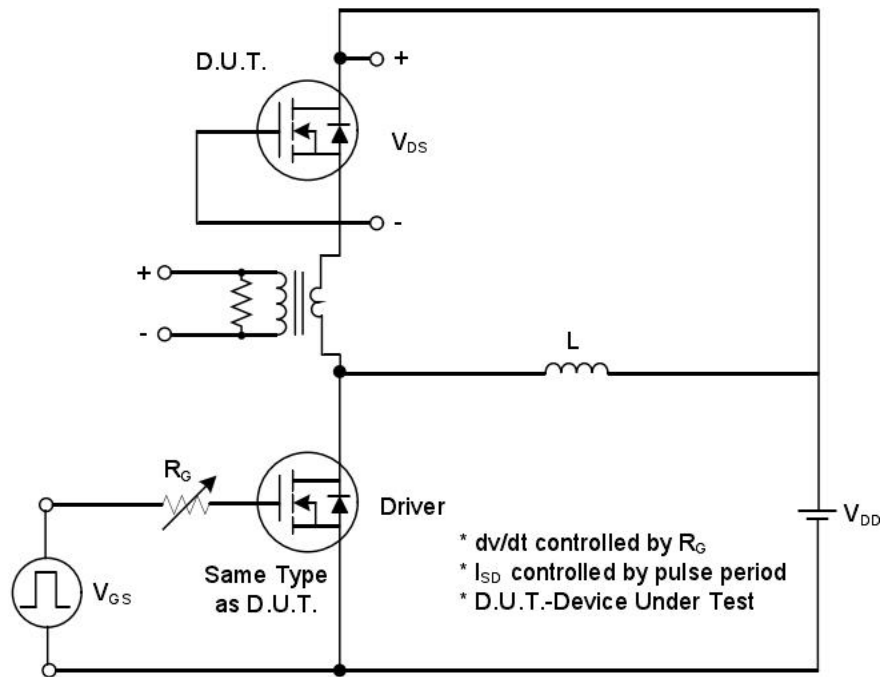
Parameter	Symbol	MAX	Units
Thermal resistance, Channel to Case	$R_{th(ch-c)}$	0.48	$^\circ\text{C}/\text{W}$
Maximum Power Dissipation	P_D	312	W

Electrical Characteristics ($T_c=25^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	—	—	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	—	—	1	μA
		$V_{DS}=100V, V_{GS}=0V$	—	—	100	
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	—	—	± 100	nA
On Characteristics						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	—	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	—	5.0	7.0	m Ω
Gate Resistance	R_g	$V_{GS}=0V, V_{DS}$ Open, $f=1\text{MHz}$	—	2.0	5.0	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $f=1.0\text{MHz}$	9000	13000	17000	pF
Output Capacitance	C_{oss}		200	550	1000	pF
Reverse Transfer Capacitance	C_{rss}		100	440	800	pF
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=20A,$ $V_{GS}=10V, R_{GEN}=3\Omega$	—	950	—	ns
Turn-On Rise Time	t_r		—	166	—	ns
Turn-Off Delay Time	$t_{d(off)}$		—	300	—	ns
Turn-Off Fall Time	t_f		—	150	—	ns
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=30A$ $V_{GS}=10V$	—	250	300	nC
Gate-Source Charge	Q_{gs}		—	65	120	nC
Gate-Drain Charge	Q_{gd}		—	70	120	nC
Drain-Source Body Diode Characteristics and Maximum Ratings						
Continuous Diode Forward Current	I_S		—	—	180	A
Pulsed Diode Forward Current	I_{SM}		—	—	720	A
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$	—	—	1.3	V
Reverse Recovery Time	t_{rr}	$V_D=30V, I_F=1A,$ $dI_F/dt=100A/\mu s, (\text{Note3})$	—	74	120	ns
Reverse Recovery Charge	Q_{rr}		—	135	200	nC

Notes

1. Repetitive Rating: pulse width limited by maximum junction temperature.
2. $L=0.5\text{mH}$, starting $T_J=25^\circ\text{C}$.
3. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

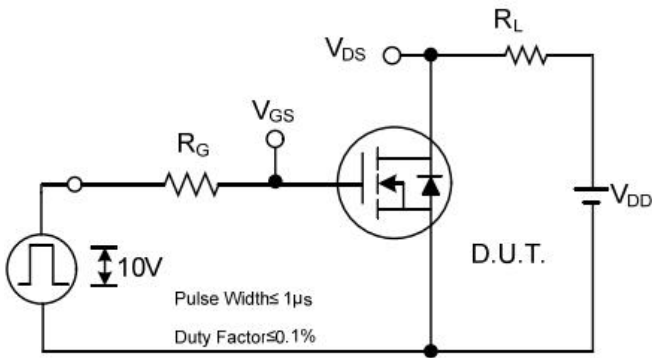
RATING AND CHARACTERISTIC CURVES



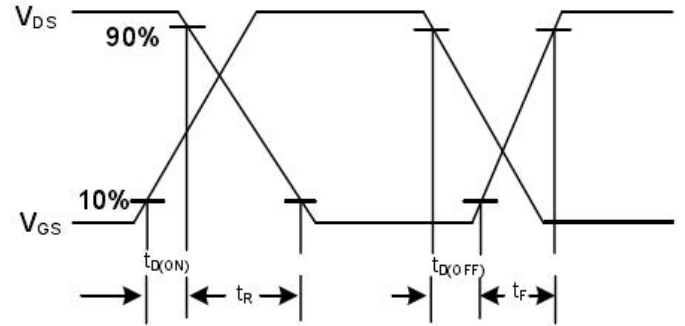
Peak Diode Recovery dv/dt Test Circuit



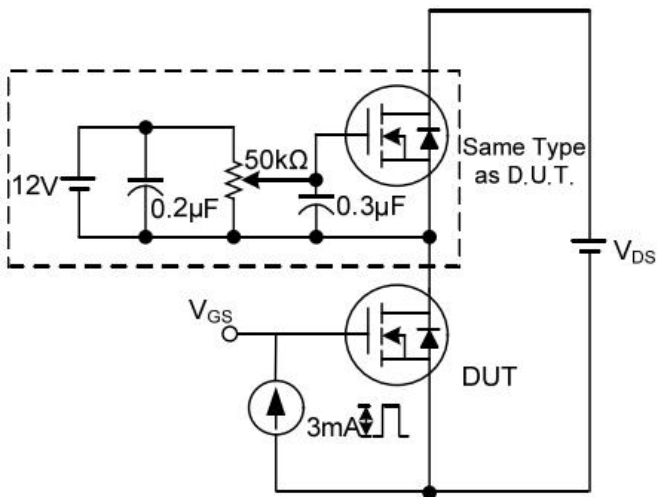
Peak Diode Recovery dv/dt Waveforms



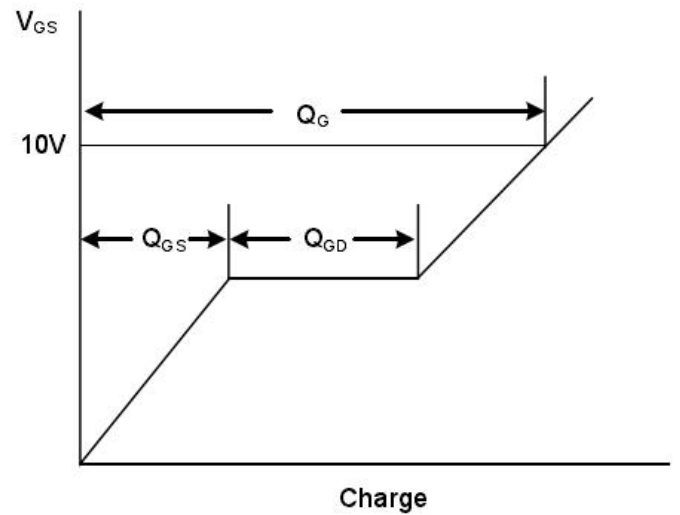
Switching Test Circuit



Switching Waveforms



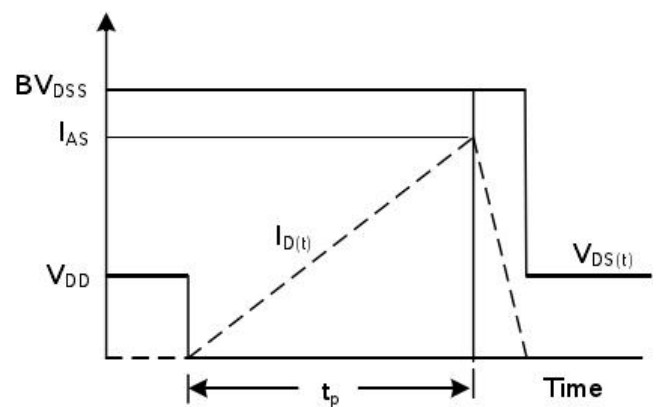
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

RATING AND CHARACTERISTIC CURVES

Figure.1 Typical Output Characteristics

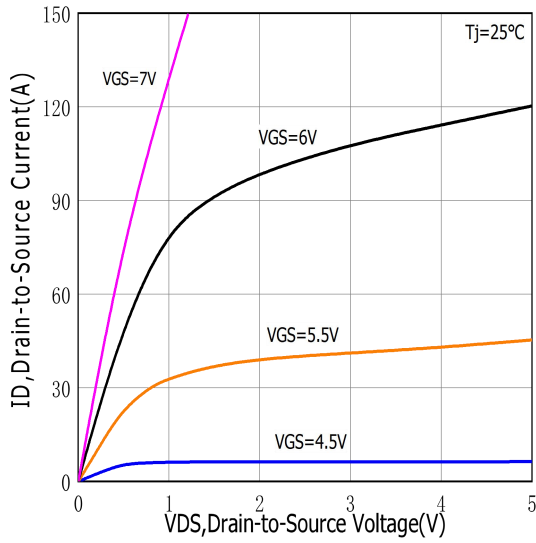


Figure.2 Typical Gate Charge vs Gate to Source Voltage

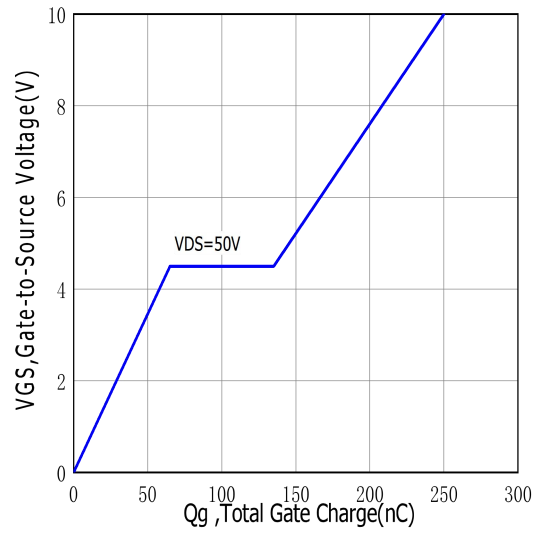


Figure.3 Typical Body Diode Transfer Characteristics

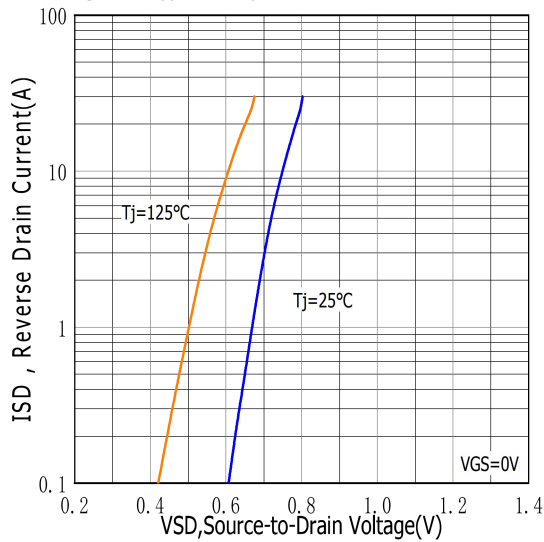


Figure.4 Typical Capacitance vs Drain to Source Voltage

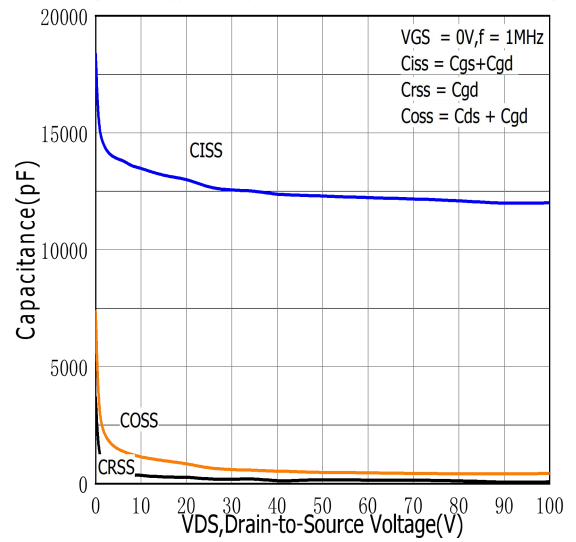


Figure.5 Typical Breakdown Voltage vs Junction Temperature

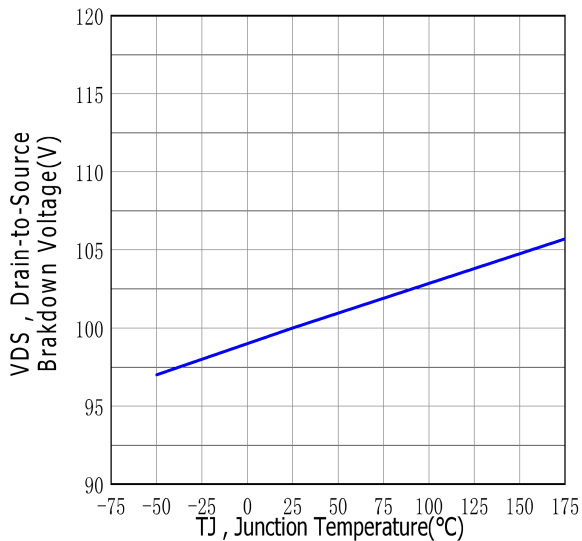


Figure.6 Typical Drain to Source on Resistance vs Junction Temperature

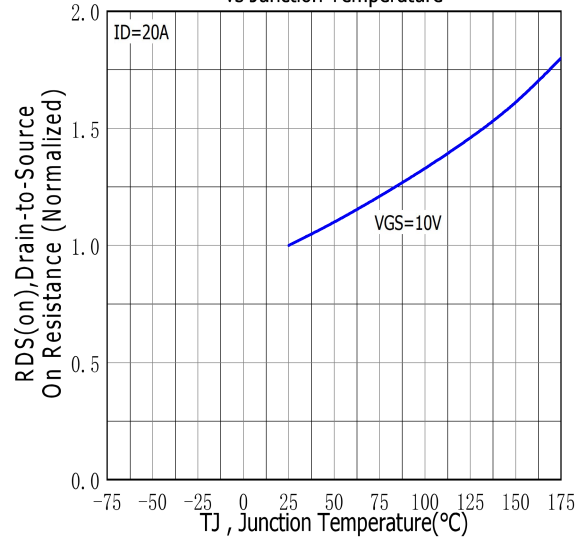


Figure.7 Maximum Forward Bias Safe Operating Area

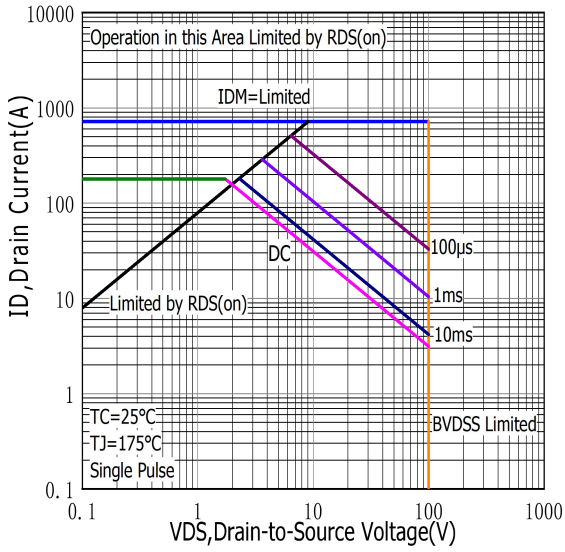


Figure.8 Typical Drain to Source ON Resistance vs Drain Current

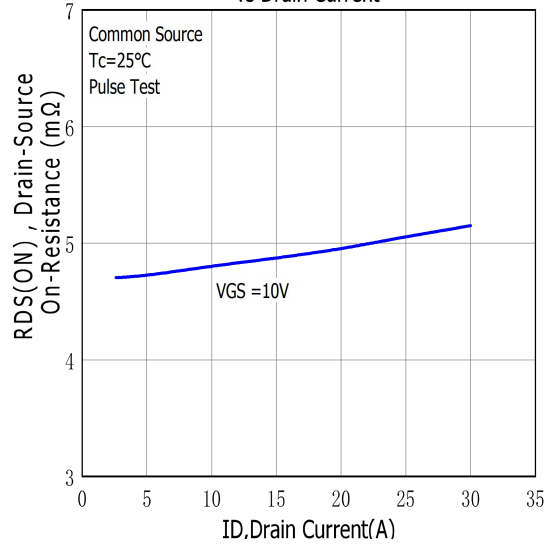


Figure.9 Maximum EAS vs Channel Temperature

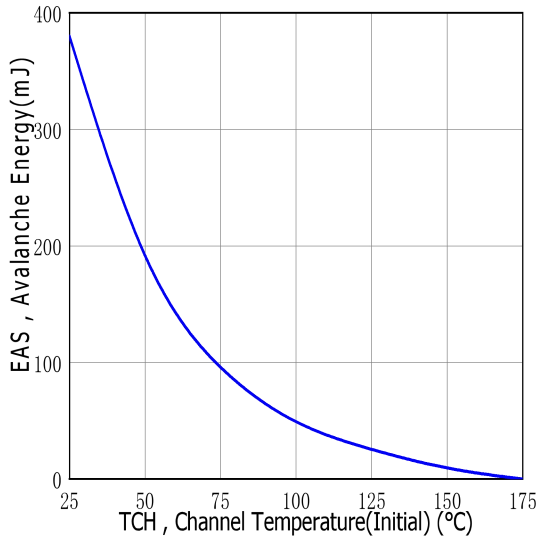


Figure.10 Typical Threshold Voltage vs Case Temperature

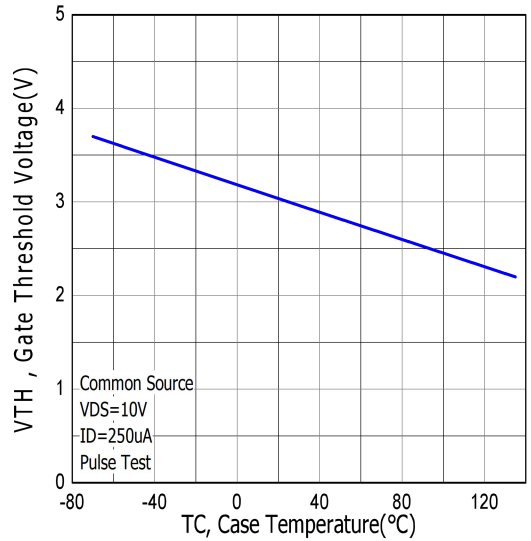


Figure.11 Maximum Effective Thermal Impedance, Junction to Case

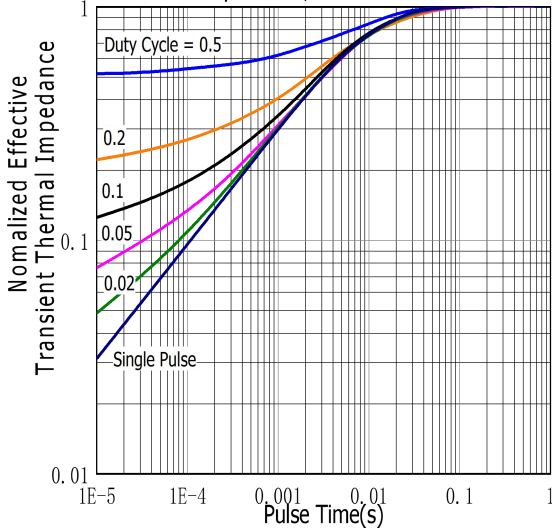
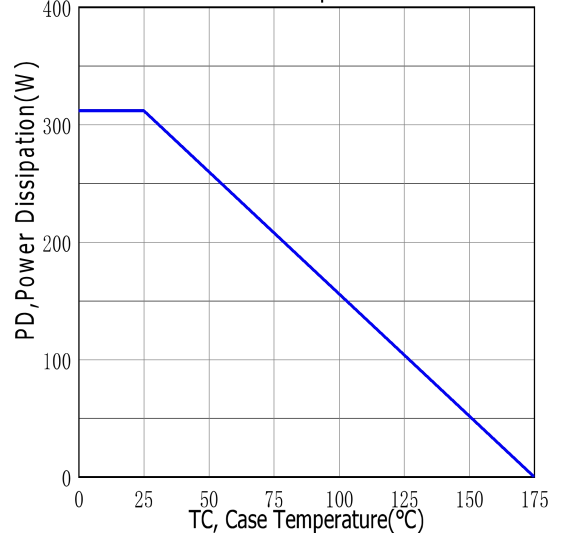
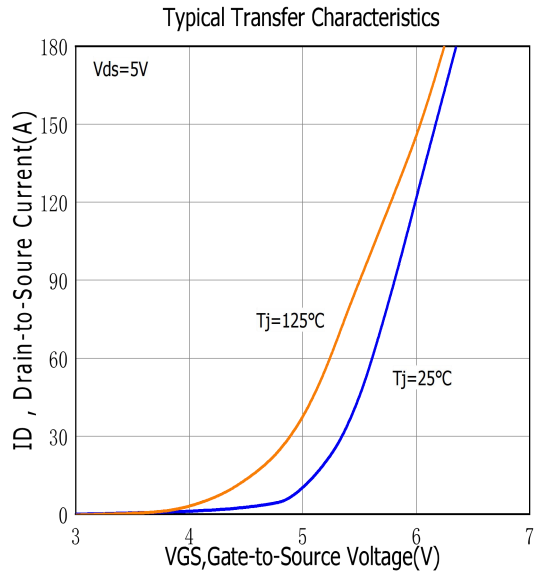
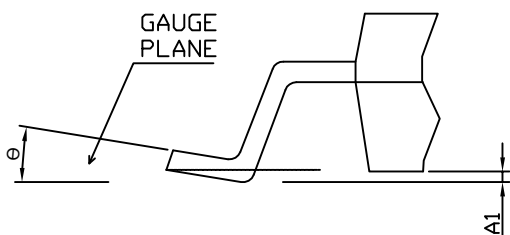
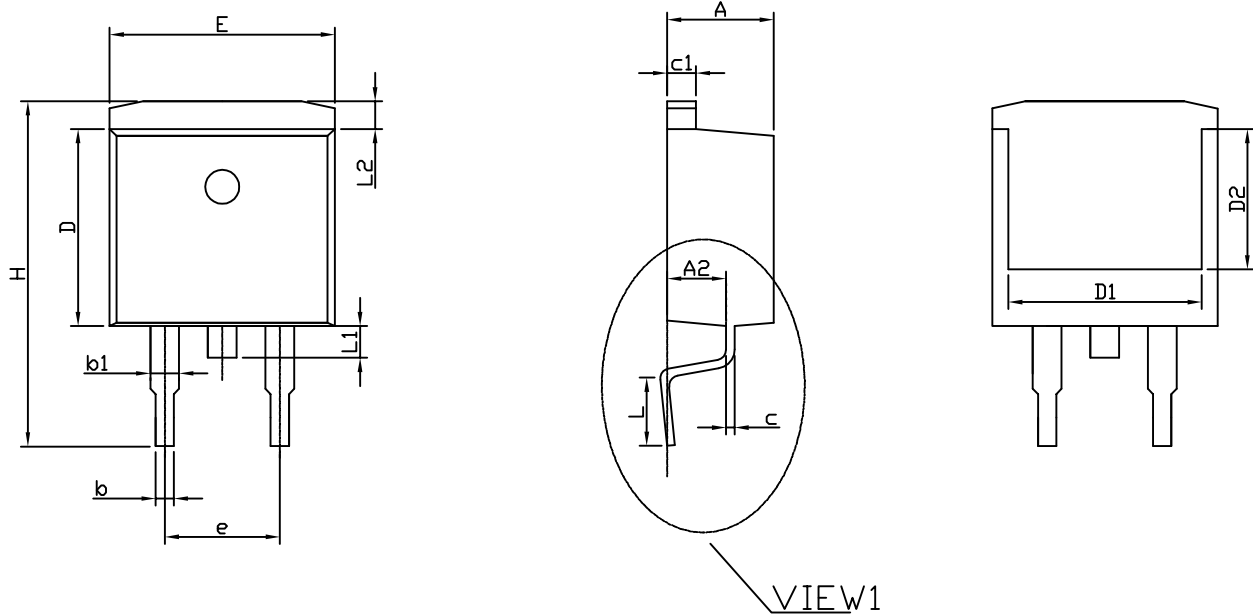


Figure.12 Maximum Power Dissipation vs Case Temperature



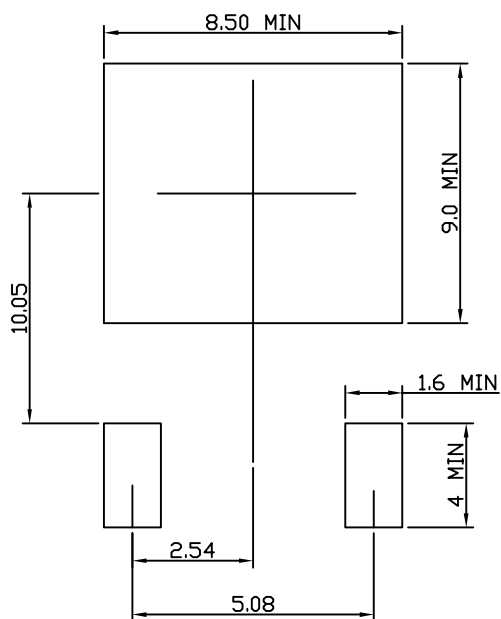


TO-263CB-2L PACKAGE OUTLINE



VIEW1

RECOMMENDED LAND PATTERN



UNIT:mm

	MIN	NOM	MAX
A	4.40	4.60	4.80
A1	0.05	0.15	0.30
A2	2.25	2.40	2.55
b	0.72	0.82	0.92
b1	1.12	1.27	1.42
c	0.40	0.50	0.60
c1	1.20	1.30	1.40
D	8.80	9.10	9.40
D1	7.75	7.95	8.15
D2	6.55	6.75	6.95
E	9.65	10.00	10.35
e		5.08BCS	
H	14.70	15.10	15.60
L	2.30	2.45	2.60
L1	1.20	1.40	1.60
L2	0.95	1.10	1.30
θ	0°	7°	8°